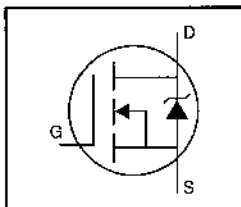


### HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- 175°C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



$$V_{DS} = 100V$$

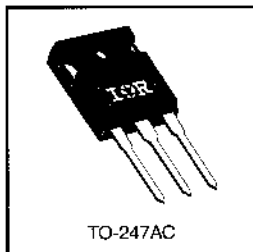
$$R_{DS(on)} = 0.055\Omega$$

$$I_D = 41A$$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.



DATA  
SHEETS

### Absolute Maximum Ratings

|                             | Parameter                                | Max.                  | Units |
|-----------------------------|------------------------------------------|-----------------------|-------|
| $I_D$ @ $T_C = 25^\circ C$  | Continuous Drain Current, $V_{GS} @ 10V$ | 41                    | A     |
| $I_D$ @ $T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 29                    |       |
| $I_{DM}$                    | Pulsed Drain Current ①                   | 160                   |       |
| $P_D$ @ $T_C = 25^\circ C$  | Power Dissipation                        | 230                   | W     |
|                             | Linear Derating Factor                   | 1.5                   | W/°C  |
| $V_{GS}$                    | Gate-to-Source Voltage                   | $\pm 20$              | V     |
| $E_{AS}$                    | Single Pulse Avalanche Energy ②          | 830                   | mJ    |
| $I_{AR}$                    | Avalanche Current ③                      | 41                    | A     |
| $E_{AR}$                    | Repetitive Avalanche Energy ④            | 19                    | mJ    |
| dv/dt                       | Peak Diode Recovery dv/dt ⑤              | 5.5                   | V/ns  |
| $T_J$                       | Operating Junction and                   | -55 to +175           | °C    |
| $T_{STG}$                   | Storage Temperature Range                |                       |       |
|                             | Soldering Temperature, for 10 seconds    | 300 (1.6mm from case) |       |
|                             | Mounting Torque, 6-32 or M3 screw        | 10 lbf·in (1.1 N·m)   |       |

### Thermal Resistance

|           | Parameter                           | Min. | Typ. | Max. | Units |
|-----------|-------------------------------------|------|------|------|-------|
| $R_{JC}$  | Junction-to-Case                    | —    | —    | 0.65 | °C/W  |
| $R_{JCS}$ | Case-to-Sink, Flat, Greased Surface | —    | 0.24 | —    |       |
| $R_{JA}$  | Junction-to-Ambient                 | —    | —    | 40   |       |

Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

|                                 | Parameter                            | Min. | Typ. | Max.  | Units    | Test Conditions                                                     |
|---------------------------------|--------------------------------------|------|------|-------|----------|---------------------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 100  | —    | —     | V        | $V_{GS}=0V$ , $I_D=250\mu A$                                        |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.14 | —     | V/°C     | Reference to $25^\circ\text{C}$ , $I_D=1mA$                         |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | —    | 0.055 | $\Omega$ | $V_{GS}=10V$ , $I_D=25A$ ④                                          |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.0  | —    | 4.0   | V        | $V_{DS}=V_{GS}$ , $I_D=250\mu A$                                    |
| $g_{fs}$                        | Forward Transconductance             | 13   | —    | —     | S        | $V_{DS}=25V$ , $I_D=25A$ ④                                          |
| $I_{OSS}$                       | Drain-to-Source Leakage Current      | —    | —    | 25    | $\mu A$  | $V_{DS}=100V$ , $V_{GS}=0V$                                         |
|                                 |                                      | —    | —    | 250   |          | $V_{DS}=80V$ , $V_{GS}=0V$ , $T_J=150^\circ\text{C}$                |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 100   | nA       | $V_{GS}=20V$                                                        |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -100  |          | $V_{GS}=-20V$                                                       |
| $Q_g$                           | Total Gate Charge                    | —    | —    | 140   | nC       | $I_D=41A$                                                           |
| $Q_{gs}$                        | Gate-to-Source Charge                | —    | —    | 29    |          | $V_{DS}=80V$                                                        |
| $Q_{gd}$                        | Gate-to-Drain ("Miller") Charge      | —    | —    | 68    |          | $V_{GS}=10V$ See Fig. 6 and 13 ④                                    |
| $t_{d(on)}$                     | Turn-On Delay Time                   | —    | 16   | —     | ns       | $V_{DD}=50V$                                                        |
| $t_r$                           | Rise Time                            | —    | 120  | —     |          | $I_D=41A$                                                           |
| $t_{d(off)}$                    | Turn-Off Delay Time                  | —    | 60   | —     |          | $R_G=6.2\Omega$                                                     |
| $t_f$                           | Fall Time                            | —    | 81   | —     |          | $R_D=1.2\Omega$ See Figure 10 ④                                     |
| $L_D$                           | Internal Drain Inductance            | —    | 5.0  | —     | nH       | Between lead, 6 mm (0.25in.) from package and center of die contact |
| $L_S$                           | Internal Source Inductance           | —    | 13   | —     |          |                                                                     |
| $C_{iss}$                       | Input Capacitance                    | —    | 2800 | —     | pF       | $V_{GS}=0V$                                                         |
| $C_{oss}$                       | Output Capacitance                   | —    | 1100 | —     |          | $V_{DS}=25V$                                                        |
| $C_{rss}$                       | Reverse Transfer Capacitance         | —    | 280  | —     |          | $f=1.0MHz$ See Figure 5                                             |

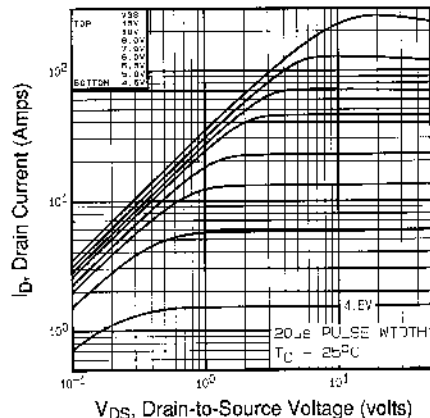


## Source-Drain Ratings and Characteristics

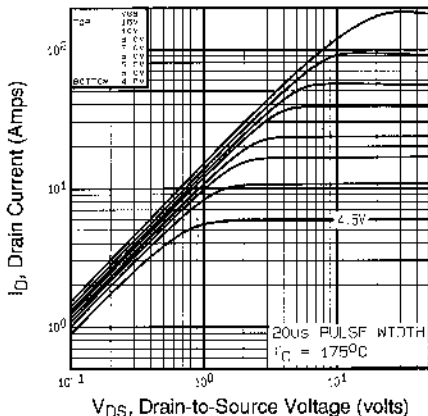
|          | Parameter                              | Min.                                                                      | Typ. | Max. | Units   | Test Conditions                                                |
|----------|----------------------------------------|---------------------------------------------------------------------------|------|------|---------|----------------------------------------------------------------|
| $I_S$    | Continuous Source Current (Body Diode) | —                                                                         | —    | 41   | A       | MOSFET symbol showing the integral reverse p-n junction diode. |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ①   | —                                                                         | —    | 160  |         |                                                                |
| $V_{SD}$ | Diode Forward Voltage                  | —                                                                         | —    | 2.5  | V       | $T_J=25^\circ\text{C}$ , $I_S=41A$ , $V_{GS}=0V$ ④             |
| $t_{rr}$ | Reverse Recovery Time                  | —                                                                         | 220  | 330  | ns      | $T_J=25^\circ\text{C}$ , $I_F=41A$                             |
| $Q_{rr}$ | Reverse Recovery Charge                | —                                                                         | 1.9  | 2.9  | $\mu C$ | $di/dt=100A/\mu s$ ④                                           |
| $t_{on}$ | Forward Turn-On Time                   | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ ) |      |      |         |                                                                |

## Notes:

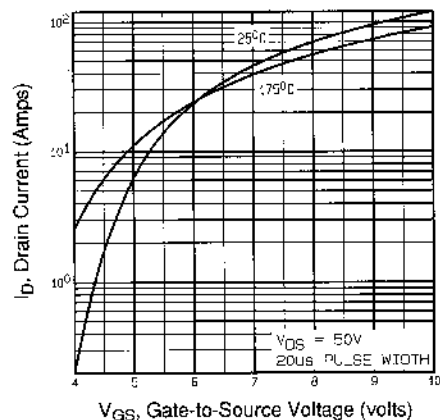
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=25V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=740\mu H$ ,  $R_G=25\Omega$ ,  $I_{AS}=41A$  (See Figure 12)
- ③  $I_{SD}\leq 41A$ ,  $di/dt\leq 300A/\mu s$ ,  $V_{DD}\leq V_{(BR)DSS}$ ,  $T_J\leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



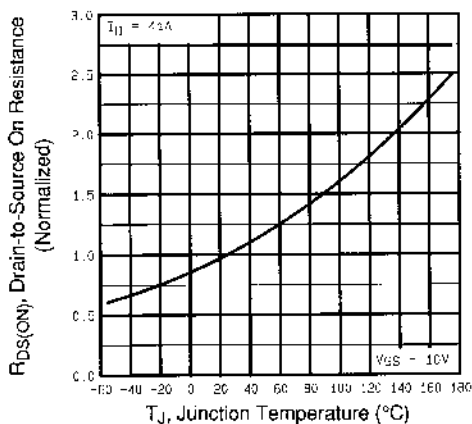
**Fig 1.** Typical Output Characteristics,  
 $T_C = 25^\circ\text{C}$



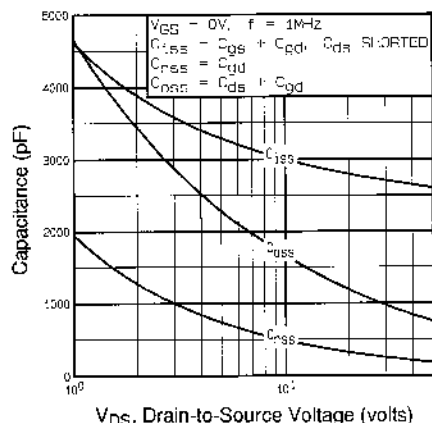
**Fig 2.** Typical Output Characteristics,  
 $T_C = 175^\circ\text{C}$



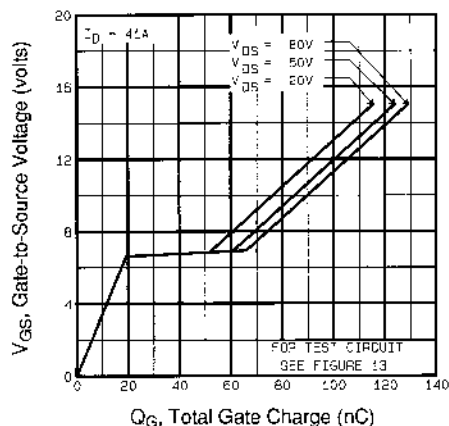
**Fig 3.** Typical Transfer Characteristics



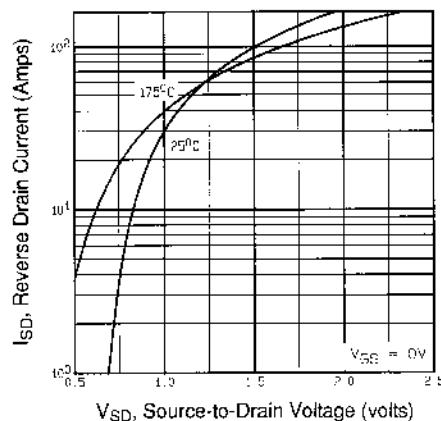
**Fig 4.** Normalized On-Resistance  
Vs. Temperature



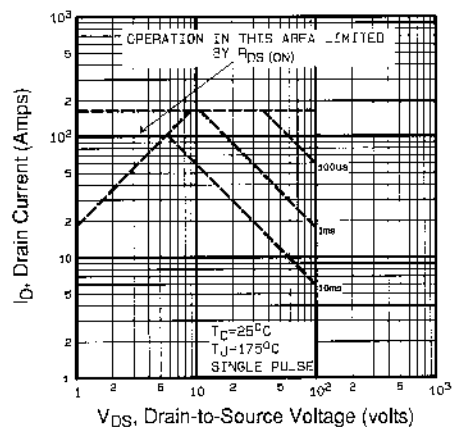
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



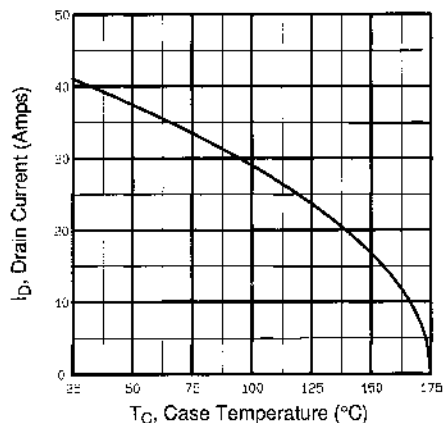
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



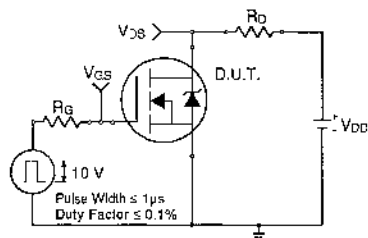
**Fig 7.** Typical Source-Drain Diode Forward Voltage



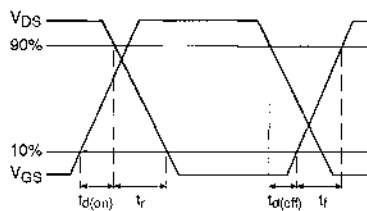
**Fig 8.** Maximum Safe Operating Area



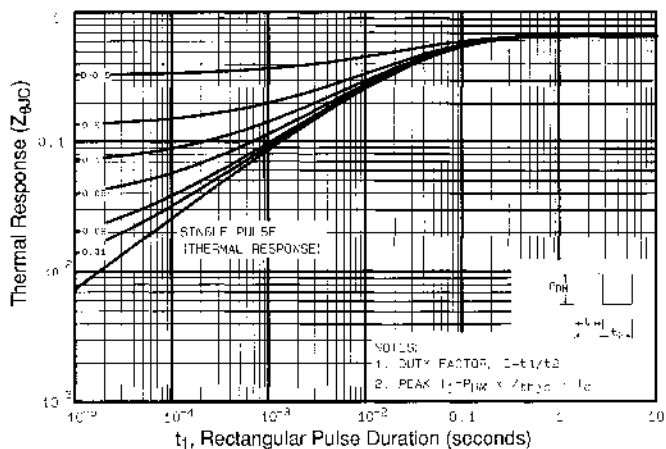
**Fig 9.** Maximum Drain Current Vs. Case Temperature



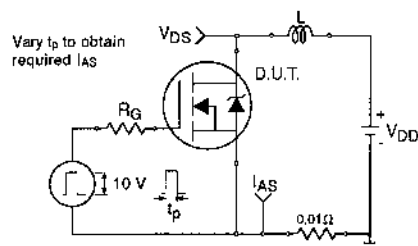
**Fig 10a.** Switching Time Test Circuit



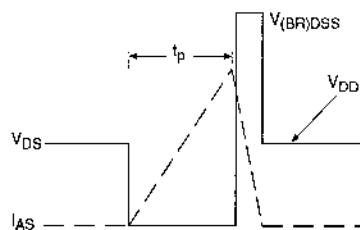
**Fig 10b.** Switching Time Waveforms



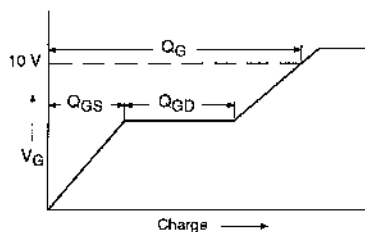
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



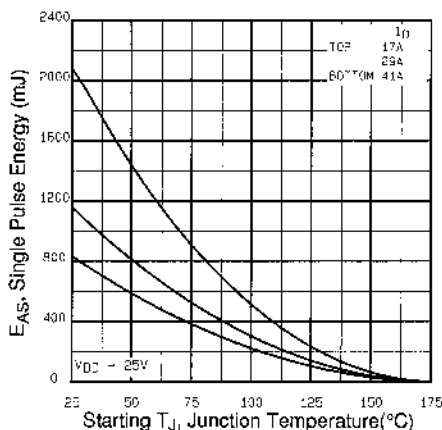
**Fig 12a.** Unclamped Inductive Test Circuit



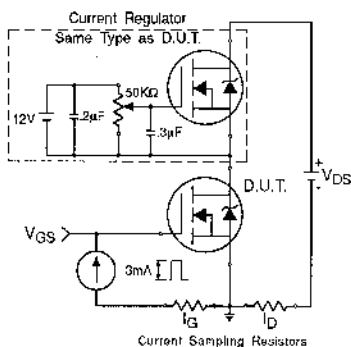
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

**Appendix A:** Figure 14, Peak Diode Recovery  $dv/dt$  Test Circuit – See page 1505

**Appendix B:** Package Outline Mechanical Drawing – See page 1511

**Appendix C:** Part Marking Information – See page 1517

**International Rectifier**